

In re: Won *et al.*
Serial No. 10/665,093
Filed: September 17, 2003
Page 2 of 6

The listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) An integrated circuit capacitor, comprising:
an electrically insulating electrode support layer comprising a mold layer on an integrated circuit substrate and an etch stop layer on the mold layer and having an opening therein, the electrically insulating electrode support layer on [[an]] the integrated circuit substrate;
a U-shaped lower electrode in the opening;
a first capacitor dielectric layer extending on an inner surface and outer portion of the U-shaped lower electrode and sealing and protecting the mold layer;
a second capacitor dielectric layer extending between the outer portion of the U-shaped lower electrode and the first capacitor dielectric between the outer portion of the U-shaped lower electrode and an inner sidewall of the opening and directly contacting a surface of the first capacitor dielectric layer opposite the U-shaped lower electrode; and
an upper electrode on the first capacitor dielectric layer.
2. (Original) The integrated circuit capacitor of Claim 1, wherein the second capacitor dielectric layer does not extend on the inner surface of the U-shaped lower electrode.

Claim 3 (Cancelled).

4. (Currently Amended) The integrated circuit capacitor of Claim [[3]] 1,
wherein the mold layer comprises silicon oxide and wherein the etch stop layer comprises at least one of silicon nitride and/or tantalum oxide.

In re: Won *et al.*
Serial No. 10/665,093
Filed: September 17, 2003
Page 3 of 6

5. (Original) The integrated circuit capacitor of Claim 1, wherein the first capacitor dielectric layer extends onto the support layer.
6. (Original) The integrated circuit capacitor of Claim 1, wherein the first capacitor dielectric layer comprises tantalum oxide, aluminum oxide (Al_2O_3), and/or Hafnium Oxide (HfO_2).
7. (Original) The integrated circuit capacitor of Claim 1, wherein the second capacitor dielectric layer comprises a dielectric material that is not etched by an oxide etchant.
8. (Currently Amended) An integrated circuit capacitor, comprising:
an electrically insulating electrode support layer comprising a mold layer on an integrated circuit substrate and an etch stop layer on the mold layer and having an opening therein, on an integrated circuit substrate;
a U-shaped lower electrode in the opening;
a first capacitor dielectric layer extending on an inner surface and outer portion of the U-shaped lower electrode and sealing and protecting the mold layer; and
a second capacitor dielectric layer extending between the outer portion of the U-shaped lower electrode and the first capacitor dielectric between the outer portion of the U-shaped lower electrode and an inner sidewall of the opening and directly contacting a surface of the first capacitor dielectric layer opposite the U-shaped lower electrode.

Claim 9 (Canceled).

10. (Previously Presented) The integrated circuit capacitor of Claim 8, wherein the second capacitor dielectric layer does not extend on the inner surface of the U-shaped lower electrode.

In re: Won *et al.*
Serial No. 10/665,093
Filed: September 17, 2003
Page 4 of 6

Claim 11 (Cancelled).

12. (Currently Amended) The integrated circuit capacitor of Claim [[11]] 8, wherein the mold layer comprises silicon oxide and wherein the etch stop layer comprises at least one of silicon nitride and/or tantalum oxide.

13. (Previously Presented) The integrated circuit capacitor of Claim 8, wherein the first capacitor dielectric layer extends onto the support layer.

14. (Previously Presented) The integrated circuit capacitor of Claim 8, wherein the first capacitor dielectric layer comprises tantalum oxide, aluminum oxide (Al_2O_3), and/or Hafnium Oxide (HfO_2).

15. (Previously Presented) The integrated circuit capacitor of Claim 8, wherein the second capacitor dielectric layer comprises a dielectric material that is not etched by an oxide etchant.